SIDDHARTH GROUP OF INSTITUTIONS :: PUTTUR Siddharth Nagar, Narayanavanam Road – 517583 **QUESTION BANK (DESCRIPTIVE) Subject with Code :** Basic Electrical and Electronics Engineering (19EE0240) **Course & Branch** : B. Tech – CSE, CSIT & AGE Year & Semester : I - B. Tech. & II - Semester Regulation :R19 PART-A UNIT-I INTRODUCTION TO ELECTRICAL ENGINEERING State and explain Ohm's law. 1. a) [L2][5M] Explain in detail about passive elements. b) [L2] [5M] Three resistances of values 20, 30 and 50 are connected in series across [L3][10M] 2. 20 V DC supply. Calculate, i) Equivalent resistance of the circuit. ii) Total current from the supply. iii) Voltage drop across each resistor. iv) Power dissipated in each resistor. Discuss about various energy sources in detail. 3. [L4][10M] 4. State and prove Kirchhoff's laws with suitable examples. [L3][5M] a) Find i_1 , i_2 , i_3 for the given circuit by using Kirchhoff's laws? b) [L3][5M] \leq 2 Ω 10 7 V 10 V 1Ω 2Ω 5. Find the current through 12Ω resistor for the given circuit using [L3][10 M] Kirchoff's laws. 2Ω 3Ω 2 V 4 V **12** Ω 3Ω

Electrical Circuits I

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7. Find the voltage to be applied across AB in order to drive a current of 5A [L3][10M] into the circuit.



8. Explain in detail about star to delta transformation of given resistive [L2][10M] netwrok.

- Explain the following in detail 9.
 - i) Resistive networks
 - ii) Inductive networks
 - iii) Capacitive networks

Define RMS value, 10 a)

[L1][2 M] **b**) Define average value, [L1][2 M] [L1][2 M] Define form factor. c) [L1][2 M] Define peak factor. d) [L1][2 M] Prove that the form factor of the sinusoidal wave is 1.11. e)

[L2][10M]

UNIT - II **NETWORK THEOREMS & TWO PORT NETWORKS**

State Super position theorem 1. a)

[L1][2M]

b) Calculate the current in 20Ω resistor in the given circuit using super position [L3][8M] theorem.



2. State Thevenin's theorem a)

[L1][2 M] [L3] [8M]

b) Find the Thevenin's equivalent circuit across AB for the circuit shown. 3Ω



3.	a)	State Norton's theorem.	[L1] [2M]
	b)	Find Norton's equivalent circuit across AB for the circuit shown.	[L3] [8M]

b) Find Norton's equivalent circuit across AB for the circuit shown.



4. Determine the maximum power delivered to the load resistance R_L [L3][10M]





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4.	a)	Explain about constructional details of dc motor.	[L2][6 M]	
	b)	A 6 pole lap wound shunt motor has 500 conductors, the armature and shunt field resistances are 0.05 Ω and 25 Ω , respectively. Find the speed of the motor if it takes 120 A from dc supply of 100 V. Flux per pole is 20 mWb.	[L3][4 M]	
5		Briefly discuss about various types of DC motors with neat sketches.	[L2][10M]	
6.	a)	Derive EMF equation of a transformer	[L2][6 M]	
	b)	A 100 kVA, 11000/400 V, 50 Hz transformer has 40 secondary turns. Calculate the number of primary turns and primary and secondary currents.	[L3][4 M]	
7.	a)	Explain constructional details of transformer.	[L2][6M]	
	b)	A 20 kVA, 2000/200 V, 50 Hz transformer has 66 secondary turns. Calculate the number of primary turns and primary and secondary currents. Neglect losses.	[L3][4 M]	
8.		Explain in detail about various transformer losses.	[L2][10M]	
9.	a)	Derive the condition for maximum efficiency of the transformer.	[L2][5 M]	
	b)	Discuss about the voltage regulation of the transformer.	[L2][5 M]	
10.	a)	Enumerate the types of DC motors.	[L2][2 M]	
	b)	List the application of DC motors.	[L1][2 M]	
	c)	Write the expression for transformer ration in terms voltage, current and turns	[L1][2 M]	
	d)	What is working principle of transformer?	[L1][2 M]	
	e)	Enumerate the various losses associated with transformer.	[][]	
			Prepared by:	
PART-B				

<u>UNIT –I</u> <u>SEMICONDUCTOR DEVICES</u> <u>Essay Answer (10 mark) Questions</u>

1. a) Distinguish between conductors, semiconductors and insulators.		
b) Draw the atomic structure of a semiconductor and explain why an intrinsic semiconductor		
is relatively a poor conductor of electricity.	[L3][5M]	
2. Discuss the conduction properties of semiconductors and explain the process of electron hole		
Pair generation and recombination.	[L3][10M]	
3. Distinguish between intrinsic and extrinsic semiconductors and explain the process of conduction		
In each of them.	[L2][10M]	
4. a) What is Doping? Describe P-and N-type semiconductors?	[L2][5M]	
b) Explain the behavior of PN junction diode.	[L2][5M]	
5. Describe the working of a PN junction diode when it is connected in forward bias and reverse bias.		
Draw VI Characteristics of PN Junction Diode.	[L3][10M]	
6. a) Write notes on Diode Specifications and Diode Applications.	[L1][6M]	
b) Explain Drift and Diffusion currents in a PN Junction Diode.	[L2][4M]	

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7. a) With neat diagram, explain the working principle of Half Wave Rectifier.	
Draw its input and Output waveforms.	[L3][5M]
b) Derive the expression for Ripple factor and Efficiency of Half Wave Rectifier.	[L2][5M]
8. a) With neat diagram, explain the working principle of Full Wave Rectifier. Draw its input and	
Output waveforms.	[L3][[5M]
b) Derive the expression for Ripple factor and Efficiency of Full Wave Rectifier.	[L2][5M]
9. a) Draw the circuit diagram of a Bridge Rectifier and explain its operation with input	
and output waveforms.	[L3][5M]
b) Discuss the operation of full wave rectifier with capacitor filter.	[L2][5M]
10. Discuss Zener Diode breakdown mechanism. Draw the Zener diode in its reverse bias a	and
explain its Volt-Ampere characteristics.	[L3][5M]

<u>UNIT –II</u>

<u>BJT</u>

Essay Answer (10 mark) Questions

1. a) Describe in detail the working of an NPN bipolar junction transistor.		
Why is it called Bipolar?	[L2][4M]	
b) Explain with the help of diagrams various types of circuit configurations, which can b	be	
obtained from a bipolar junction transistor.	[L3][6M]	
2. a) Discuss the operation of PNP transistor with diagram	[L2][5M]	
b) If the base current in a transistor is $20\mu A$ when the emitter current is 6.4mA, what		
are the values of α and β ? Also calculate the collector current.	[L3][5M]	
3. Draw the circuit diagram for a common base circuit arrangement and plot its input and Output		
characteristics. Show the different regions of the output characteristics and explain their occurrence.		
	[L3][10M]	
4. a) Discuss with neat diagrams, the Common Emitter Configuration and its characteristics.[L2] [5M]		
b)Explain the characteristics of CE configuration	[L2][5M]	
5. Draw the circuit diagram for a common Collector circuit arrangement and plot its input and Output		
characteristics. Show the different regions of the output characteristics and explain their	r occurrence.	
	[L3][10M]	
6. a) Explain the functioning of Common Collector Configuration of BJT. State why this arrangement		
is also called an emitter follower circuit.	[L3][5M]	

QUESTION BANK 2020 b) Compare the characteritcs of BJT CB, CE and CC transistor configurations. [L2][[5M] 7. a) Derive the relationship between IC,IB,IE of BJT configurations. [L2][5M] b) A transistor operating in CB configuration has $I_C = 2.98$ mA, $I_E = 3.00$ mA and $I_{CO} = 0.01$ mA. What current will flow in the collector circuit for this transistor when connected in CE configuration with a base current of 30µA? [L3][5M] 8. With neat circuit diagram and equations, explain Fixed Bias circuit of BJT. [L2][10M] 9. Describe the Voltage Divider Bias Network of BJT with diagram and equations. [L2][10M] 10. a) write the application of a transistor and explain the transistor acts a switch . [L2][5M] b) Explain in detail the transistor working as a amplifier [L2][[5M]

<u>UNIT –III</u>

JFET & MOSFETS

Essay Answer (10 mark) Q

1. a) Explain about the JFET and draw the construction of JFET	[L3][5M]
b) Explain the operation of JFET	[L3][5M]
2. a) Explain the construction and principle of operation of N-channel JFET.	[L3][5M]
b) Define the JFET Volt-Ampere Characteristics and determine FET parameters	s. [L3][5M]
3. a) Explain the output characteristics of JFET .	[L2][5M]
b) Explain the transfer characteristics of JFET	[L2][5M]
4. a)Discuss the configuration of JFET	[L2][4M]
b) Explain the CD configuration and draw its construction	[L3][6M]
5. Explain the CS configuration ? With construction and its operation	[L3][10M]
6. Explain the CG configuration ? With construction and its operation	[L3][5M]
7. a)Write the JFET applications	[L1][4M]
b) Explain the working of JFET as amplifier	[L2][6M]
8. a) Explain how the JFET working as a switch	[L2][5M]
b) Write the comparision BJT and JFET.	[L1][[5M]
9. a) Draw the construction of EMOSFET and explain its operation	[L3][5M]
	E 36 3
b) Expalin the operation DMOSFET	[L3][5M]
b) Expalin the operation DMOSFET10.a) Explain the static characteristics of MOSFET and draw its characteristics	[L3][5M] [L3][6M]

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